

Title (en)  
METHOD FOR PRODUCING A SPACER STRUCTURE

Title (de)  
VERFAHREN ZUR HERSTELLUNG EINER SPACERSTRUKTUR

Title (fr)  
PROCEDE POUR PRODUIRE UNE STRUCTURE D'ESPACEMENT

Publication  
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Application  
**EP 03737879 A 20030514**

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Abstract (en)  
[origin: WO03107405A1] The invention relates to a method for producing a spacer structure. According to the inventive method, a gate insulation layer (2) comprising a gate deposition inhibition layer (2A), a gate layer (3) and a covering deposition inhibition layer (4) are formed on a semiconductor substrate (1), and the gate layer (3) and the covering deposition inhibition layer (4) are structured in such a way as to form stacks of gates (G). According to the invention, an insulation layer (6) is selectively deposited using the deposition inhibition layers (2A, 4) in order to form a spacer structure in a highly precise manner.

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Citation (search report)  
See references of WO 03107405A1

Citation (examination)  
• US 6080607 A 20000627 - CHANG CHUN YEN [TW], et al  
• ELBEL N ET AL: "A New STI Process Based on Selective Oxide Deposition", VLSI TECHNOLOGY 1998 - SYMPOSIUM ON VLSI TECHNOLOGY - DIGEST OF TECHNICAL PAPERS, 11 June 1998 (1998-06-11), Honolulu, Hawaii, pages 208 - 209, XP000802805

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